Figure 7: Temperature dependences of voltage for fixed currents through a Ni-silicide/poly-Si Schottky diode and temperature coefficient of signal (voltage) for each branch of $I$–$V$ characteristics: (a) forward and (b) reverse biases (the legends represent the currents in $\mu$A for each line); (c, d) temperature coefficient of voltage for each branch of $I$–$V$ characteristics vs fixed current through the structure; to derive the graph (d), the curves in the panel (b) were linearized in the interval from 20 to 60°C; negative and positive values of $I$ in panels (c) and (d) correspond to forward and reverse biasing, respectively.